

Features

- Uses CRM(CQ) advanced SkyMOS3 technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent $Q_g \times R_{DS(on)}$ product(FOM)
- Qualified according to JEDEC criteria

Applications

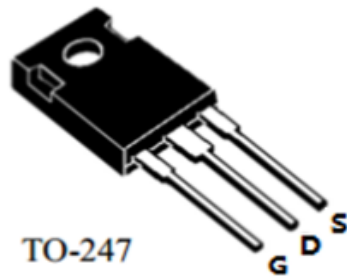
- Motor control and drive
- Battery management
- UPS (Uninterruptible Power Supplies)

Product Summary

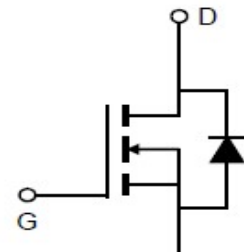
V_{DS}	200V
$R_{DS(on)}$	8.3mΩ
I_D	100A

100% DVDS Tested

100% Avalanche Tested



SFW096N200I3



Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
SFW096N200I3	096N200I3	TO-247	Tube	N/A	N/A	30pcs

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	200	V
Continuous drain current $T_C = 25^\circ\text{C}$ (Silicon limit) $T_C = 25^\circ\text{C}$ (Package limit) $T_C = 100^\circ\text{C}$ (Silicon limit)	I_D	100 120 63	A
Pulsed drain current ($T_C = 25^\circ\text{C}$, t_p limited by T_{jmax})	$I_{D \text{ pulse}}$	400	A
Avalanche energy, single pulse ($L=0.5\text{mH}$, $R_g=25\Omega$)	E_{AS}	400	mJ
Gate-Source voltage	V_{GS}	± 20	V
Power dissipation ($T_C = 25^\circ\text{C}$)	P_{tot}	250	W
Operating junction and storage temperature	T_j, T_{stg}	$-55 \dots +150$	$^\circ\text{C}$
Soldering temperature, wave soldering only allowed at leads (1.6mm from case for 10s)	T_{sold}	260	$^\circ\text{C}$

Thermal Resistance

Parameter	Symbol	Max	Unit
Thermal resistance, junction – case.	R_{thJC}	0.28	°C/W
Thermal resistance, junction – ambient(min. footprint)	R_{thJA}^*	62.5	

Electrical Characteristic (at $T_j = 25\text{ °C}$, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

Drain-source breakdown voltage	BV_{DSS}	200	-	-	V	$V_{GS}=0V, I_D=250\mu A$
Gate threshold voltage	$V_{GS(th)}$	2.0	3.0	4.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$
Zero gate voltage drain current	I_{DSS}	-	0.04	1	μA	$V_{DS}=200V, V_{GS}=0V$ $T_j=25\text{ °C}$
		-	-	100		$T_j=125\text{ °C}$
Gate-source leakage current	I_{GSS}	-	± 10	± 100	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	8.3	9.6	mΩ	$V_{GS}=10V, I_D=50A,$ $T_j=25\text{ °C}$ TO-247
Transconductance	g_{fs}	-	93	-	S	$V_{DS}=5V, I_D=50A$

Dynamic Characteristic

Input Capacitance	C_{iss}	-	5450	-	pF	$V_{GS}=0V, V_{DS}=100V,$ $f=1MHz$
Output Capacitance	C_{oss}	-	407	-		
Reverse Transfer Capacitance	C_{rss}	-	20	-		
Gate Total Charge	Q_G	-	69	-	nC	$V_{GS}=10V, V_{DS}=100V,$ $I_D=50A, f=1MHz$
Gate-Source charge	Q_{gs}	-	25	-		
Gate-Drain charge	Q_{gd}	-	16	-		

Turn-on delay time	$t_{d(on)}$	11	16	24	ns	$V_{DS}=100V$ $I_D=50A$ $R_G=2.7\Omega$ $V_{GS}=10V$;
Rise time	t_r	55	82	123		
Turn-off delay time	$t_{d(off)}$	37	55	110		
Fall time	t_f	56	84	126		
Gate resistance	R_G	-	3.2	-	Ω	$V_{GS}=0V, V_{DS}=0V,$ $f=1MHz$

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	0.5	0.82	1.4	V	$V_{GS}=0V, I_{SD}=50A$
Body Diode Continuous Forward Current	I_S	-	-	100	A	$T_C = 25^\circ C$
Body Diode Pulsed Current	$I_{S \text{ pulse}}$	-	-	400	A	$T_C = 25^\circ C$
Body Diode Reverse Recovery Time	t_{rr}	65	129	258	ns	$I_{SD}=50A, V_{GS}=0V,$ $dI/dt=100A/us$;
Body Diode Reverse Recovery Charge	Q_{rr}	376	752	1504	nC	

Typical Performance Characteristics

Fig 1: Output Characteristics

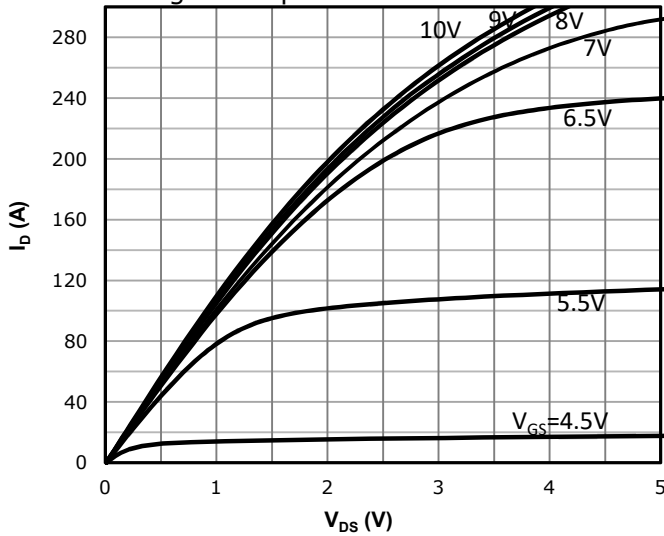


Fig 2: Transfer Characteristics

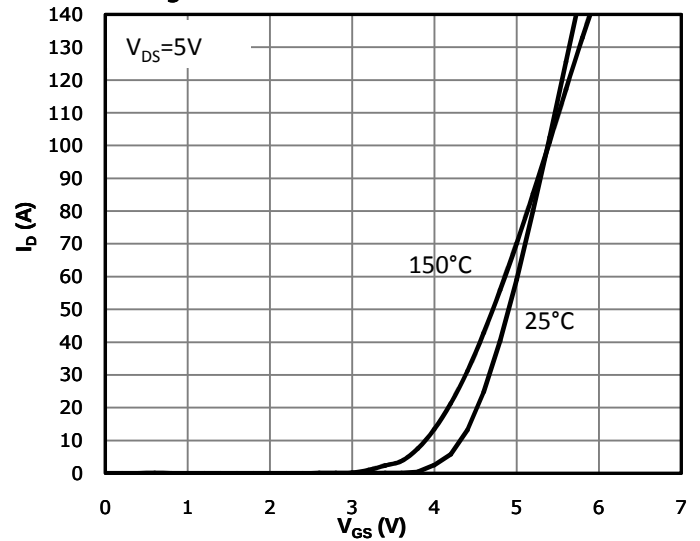


Fig 3: $R_{DS(on)}$ vs Drain Current and Gate Voltage

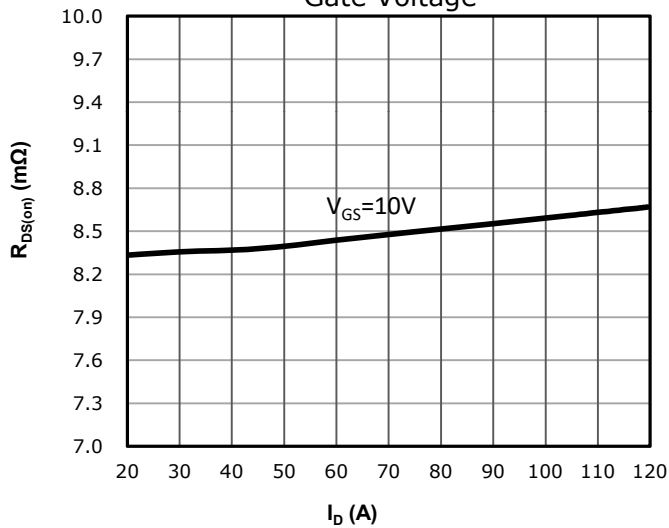


Fig 4: $R_{DS(on)}$ vs Gate Voltage

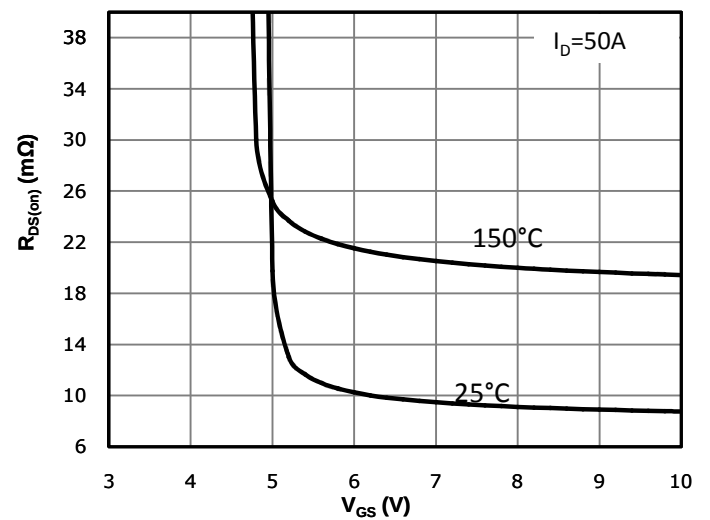


Fig 5: $R_{DS(on)}$ vs. Temperature

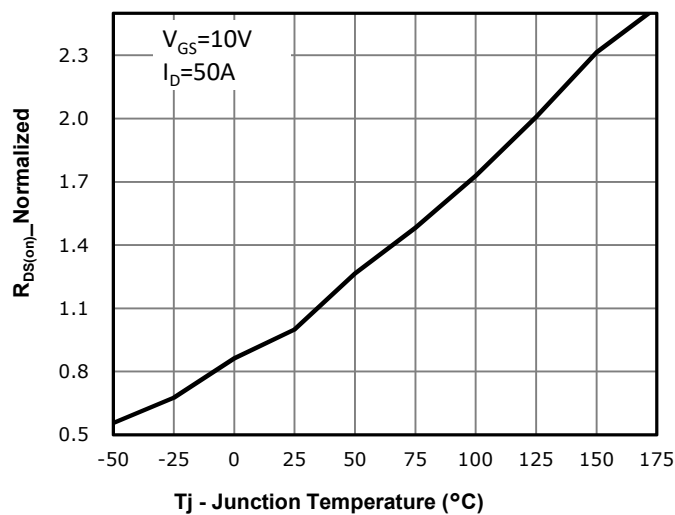


Fig 6: Capacitance Characteristics

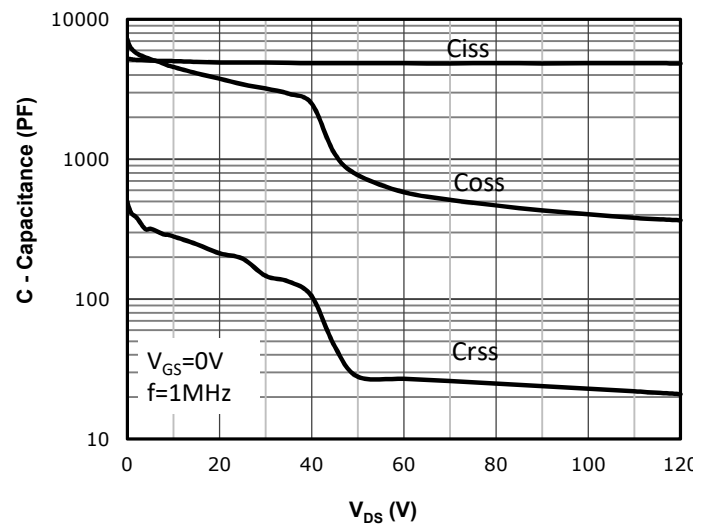


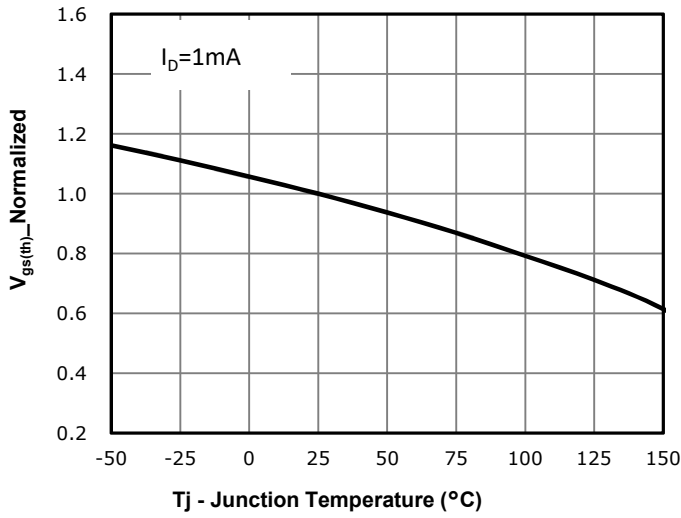
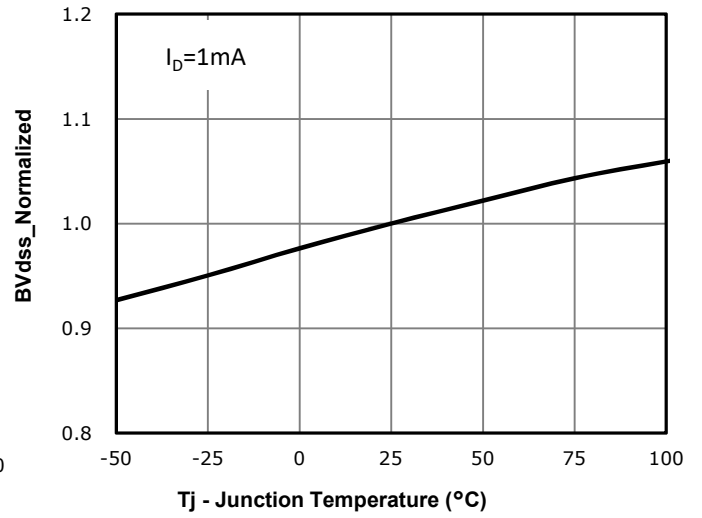
Fig 7: $V_{gs(th)}$ vs. Temperature

Fig 8: BV_{dss} vs. Temperature


Fig 9: Gate Charge Characteristics

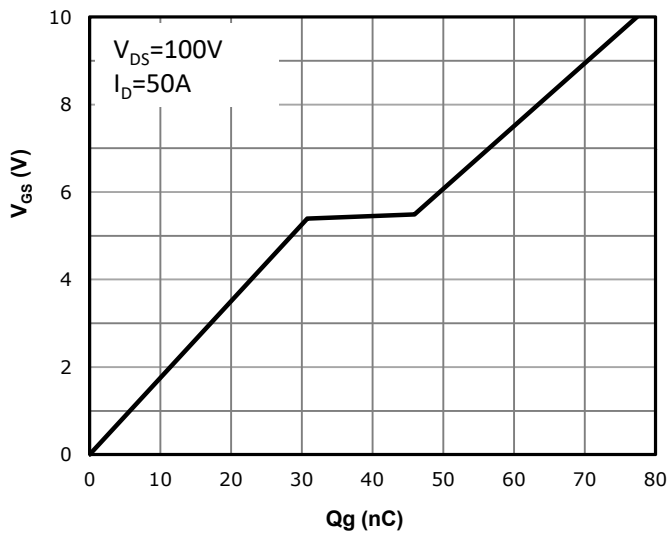


Fig 10: Body-diode Forward Characteristics

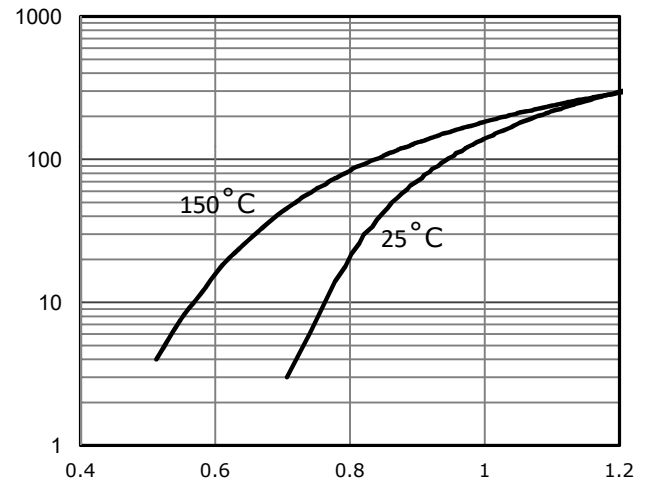


Fig 11: Power Dissipation

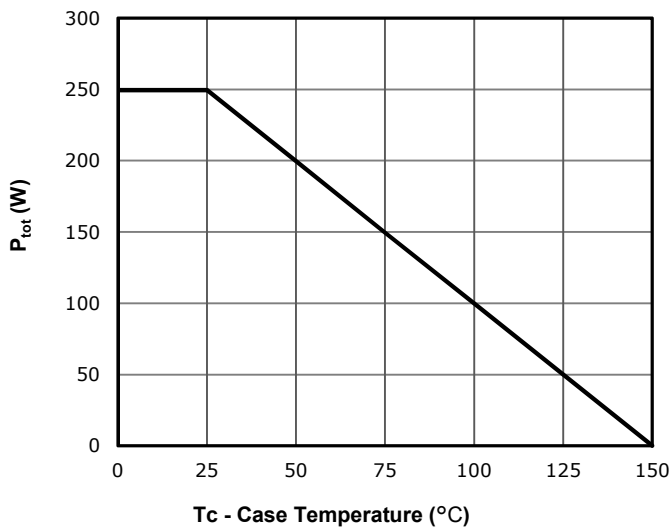


Fig 12: Drain Current Derating

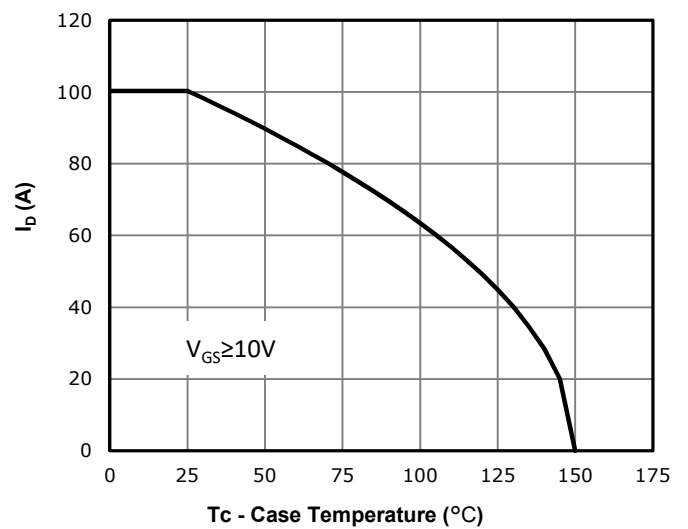


Fig 13: Safe Operating Area

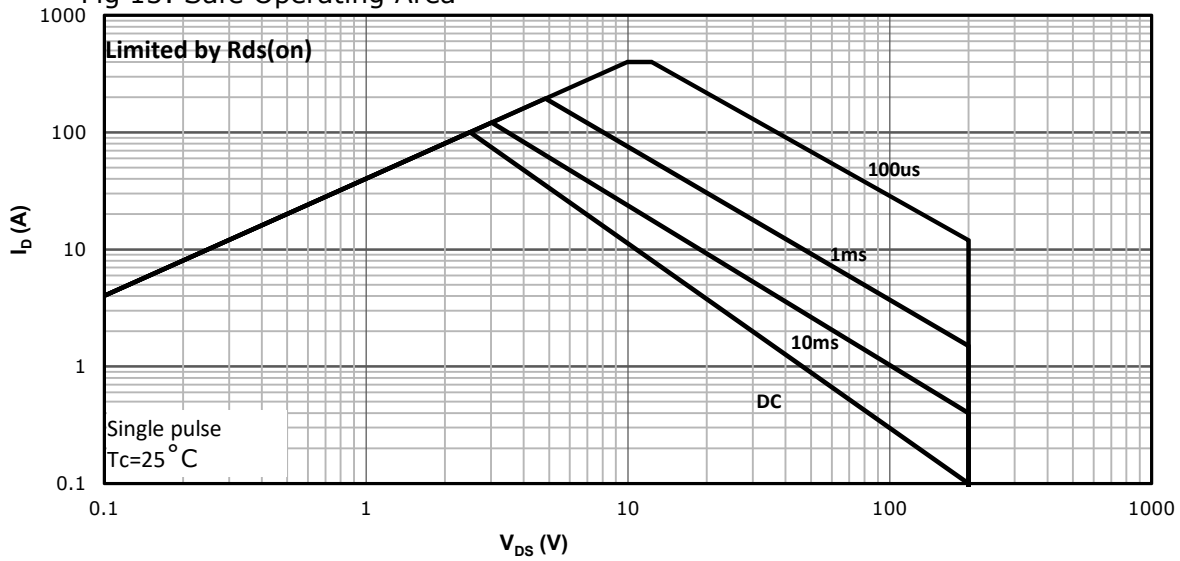
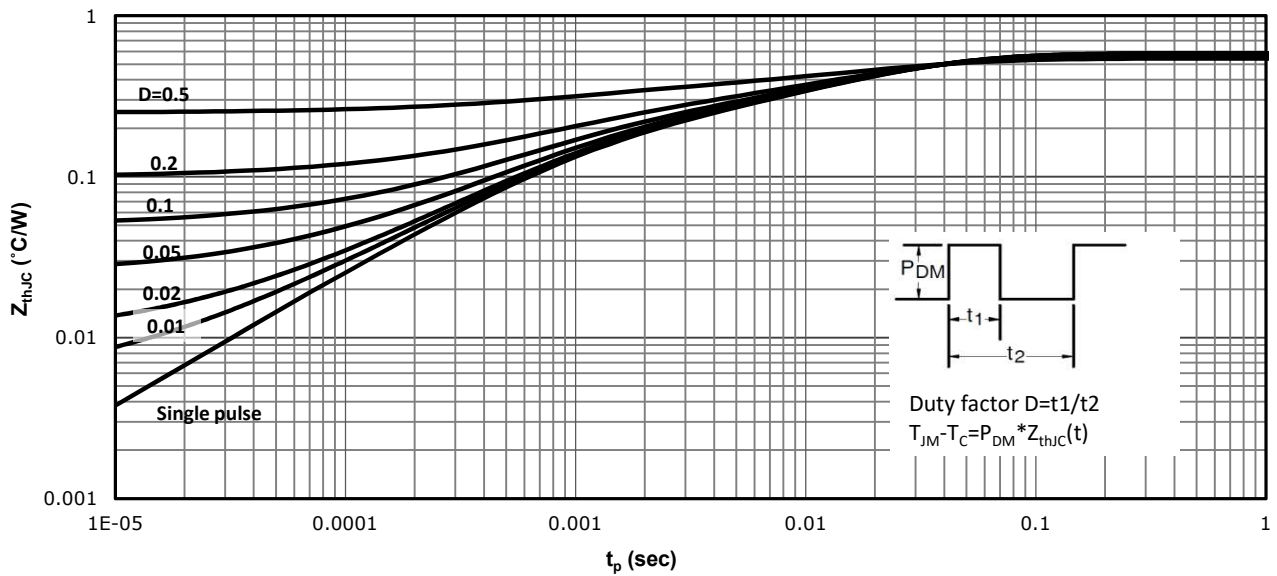
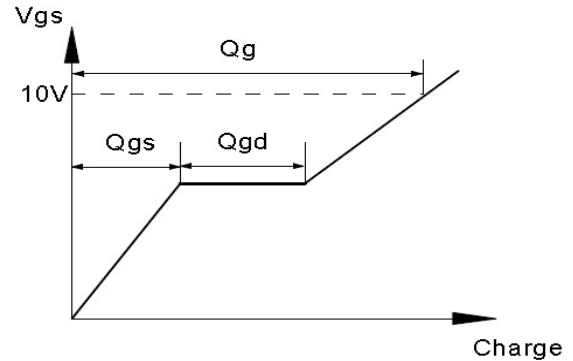
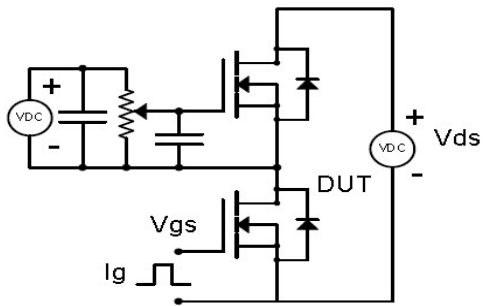


Fig 14: Max. Transient Thermal Impedance

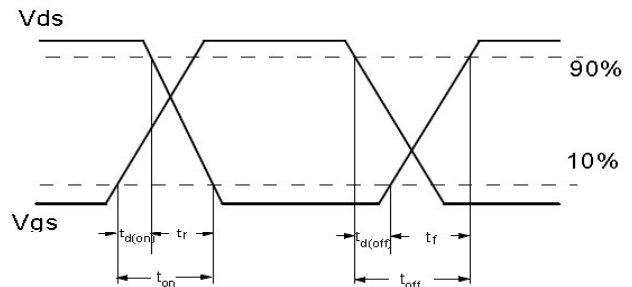
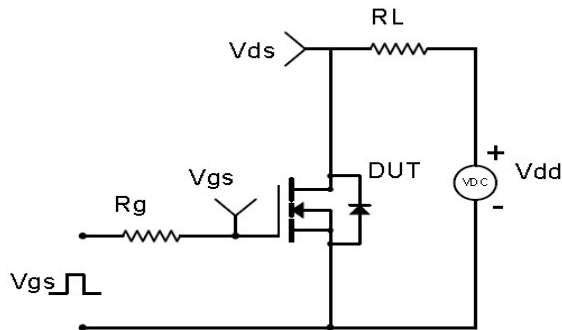


Test Circuit & Waveform

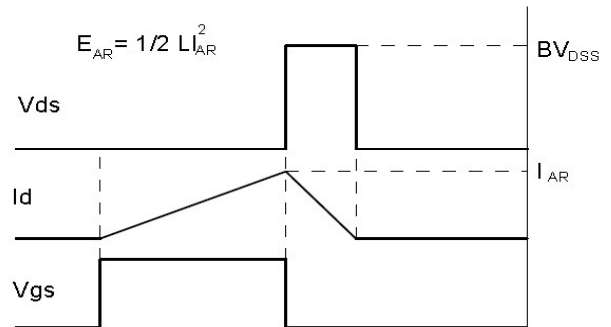
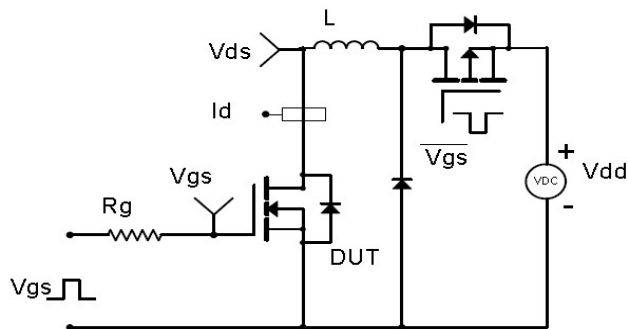
Gate Charge Test Circuit & Waveform



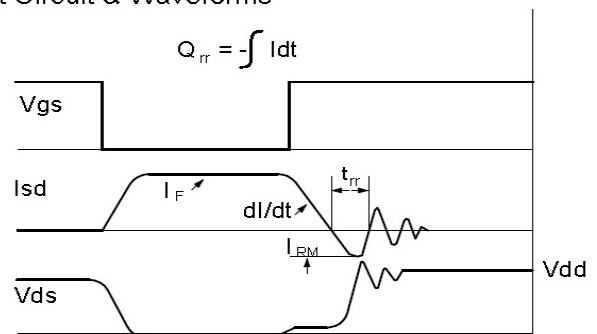
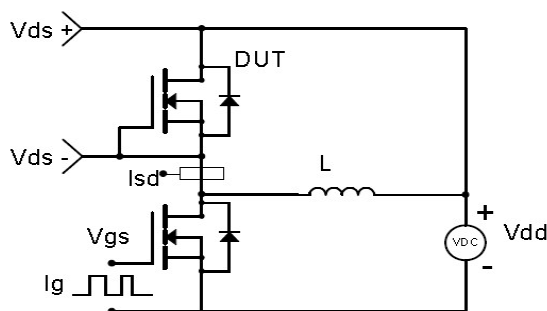
Resistive Switching Test Circuit & Waveforms

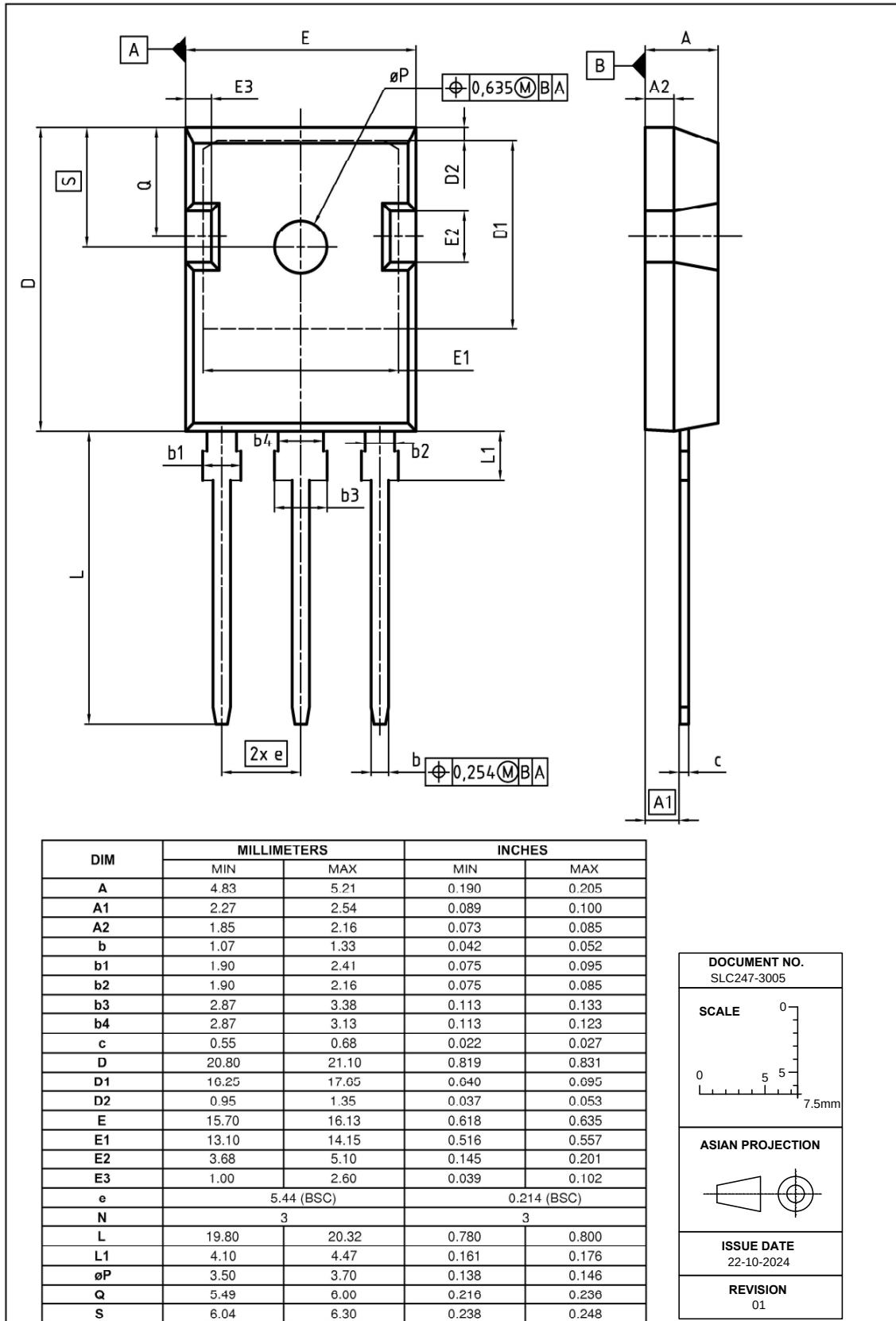


Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



PackageOutlines-TO-247


Revision History

Revision	Date	Major changes
1.0	2024-10-22	Release of formal version.

Disclaimer

Unless otherwise specified in the datasheet, the product is designed and qualified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

Scilicon Electric reserves the right to improve product design,function and reliability without notice.